



BUK9K18-40E

Dual N-channel 40 V, 19.5 mΩ logic level MOSFET

16 March 2016

Product data sheet

1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with $V_{GS(th)}$ rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

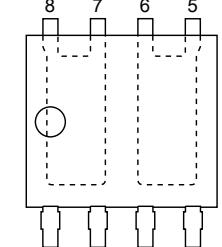
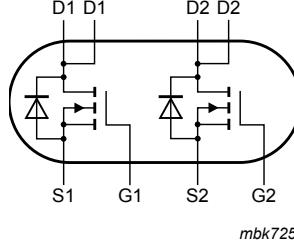
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25^{\circ}\text{C} \leq T_j \leq 175^{\circ}\text{C}$		-	-	40	V
I_D	drain current	$V_{GS} = 5\text{ V}$; $T_{mb} = 25^{\circ}\text{C}$; Fig. 2		-	-	30	A
P_{tot}	total power dissipation	$T_{mb} = 25^{\circ}\text{C}$; Fig. 1		-	-	38	W
Static characteristics FET1 and FET2							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5\text{ V}$; $I_D = 10\text{ A}$; $T_j = 25^{\circ}\text{C}$; Fig. 12		-	17.1	19.5	$\text{m}\Omega$
Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	$I_D = 10\text{ A}$; $V_{DS} = 32\text{ V}$; $V_{GS} = 10\text{ V}$; $T_j = 25^{\circ}\text{C}$; Fig. 14		-	3	-	nC

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1	 LFPAK56D (SOT1205)	 mbk725

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9K18-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9K18-40E	91840E

8. Limiting values

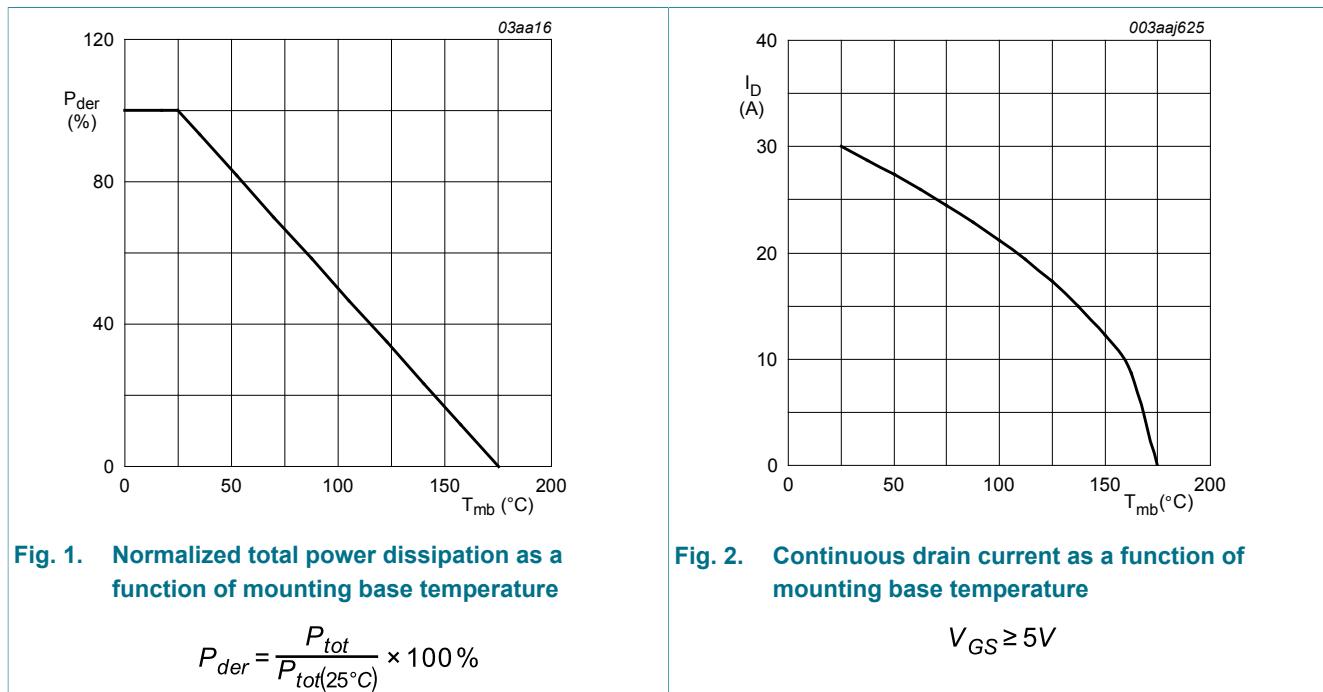
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25^{\circ}\text{C} \leq T_j \leq 175^{\circ}\text{C}$	-	40	V
V_{DGR}	drain-gate voltage	$25^{\circ}\text{C} \leq T_j \leq 175^{\circ}\text{C}; R_{GS} = 20\text{ k}\Omega$	-	40	V
V_{GS}	gate-source voltage	DC; $T_j \leq 175^{\circ}\text{C}$	-10	10	V
		Pulsed; $T_j \leq 175^{\circ}\text{C}$	[1][2]	-15	15
P_{tot}	total power dissipation	$T_{mb} = 25^{\circ}\text{C}$; Fig. 1	-	38	W
I_D	drain current	$V_{GS} = 5\text{ V}; T_{mb} = 25^{\circ}\text{C}$; Fig. 2	-	30	A
		$V_{GS} = 5\text{ V}; T_{mb} = 100^{\circ}\text{C}$; Fig. 2	-	24	A

Symbol	Parameter	Conditions		Min	Max	Unit
I_{DM}	peak drain current	pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$; Fig. 3		-	124	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode FET1 and FET2						
I_S	source current	$T_{mb} = 25^\circ\text{C}$		-	30	A
I_{SM}	peak source current	pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$		-	124	A
Avalanche Ruggedness FET1 and FET2						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 30 \text{ A}$; $V_{sup} \leq 40 \text{ V}$; $V_{GS} = 5 \text{ V}$; $T_{j(init)} = 25^\circ\text{C}$; Fig. 4	[3][4]	-	22	mJ

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T_j and or V_{GS} .
- [3] Refer to application note AN10273 for further information
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



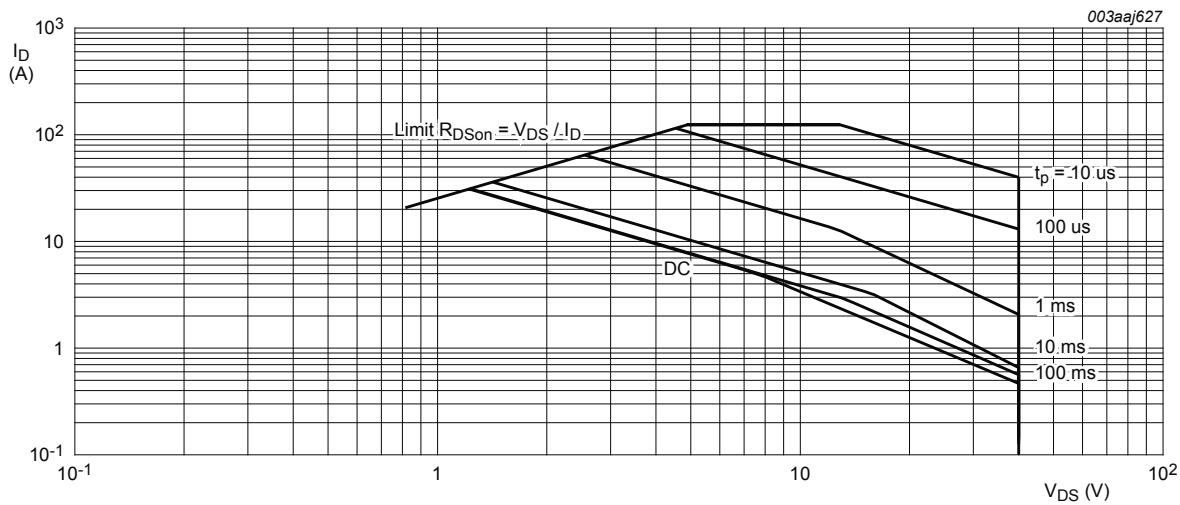


Fig. 3. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$T_{mb} = 25^\circ\text{C}$; I_{DM} is single pulse

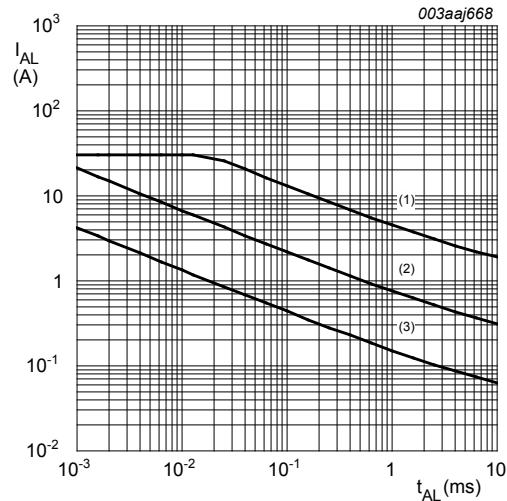


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

(1) Single-pulse; $T_j = 25^\circ\text{C}$.

(2) Single-pulse; $T_j = 150^\circ\text{C}$.

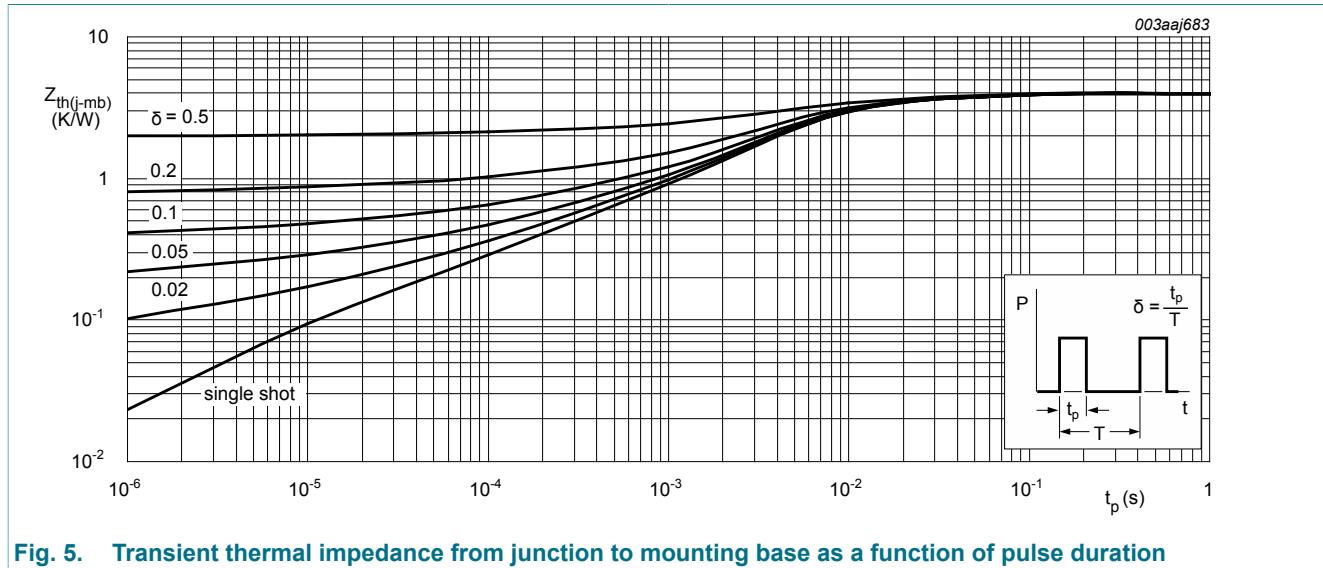
(3) Repetitive.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	3.96	K/W

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board		-	95	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics FET1 and FET2							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55^\circ C$		36	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25^\circ C$		40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25^\circ C$ Fig. 10 ; Fig. 11		1.4	1.7	2.1	V
		$I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175^\circ C$ Fig. 10 ; Fig. 11		0.5	-	-	V
		$I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55^\circ C$ Fig. 10 ; Fig. 11		-	-	2.45	V
I_{DSS}	drain leakage current	$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175^\circ C$		-	-	500	μA
		$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25^\circ C$		-	0.02	1	μA
I_{GSS}	gate leakage current	$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25^\circ C$		-	2	100	nA
		$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25^\circ C$		-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5 V; I_D = 10 A; T_j = 25^\circ C$; Fig. 12		-	17.1	19.5	$m\Omega$
		$V_{GS} = 5 V; I_D = 10 A; T_j = 175^\circ C$; Fig. 12 ; Fig. 13		-	34.37	39.2	$m\Omega$

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		$V_{GS} = 10 \text{ V}$; $I_D = 10 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 12		-	13.5	16	mΩ

Dynamic characteristics FET1 and FET2

$Q_{G(\text{tot})}$	total gate charge	$I_D = 10 \text{ A}$; $V_{DS} = 32 \text{ V}$; $V_{GS} = 10 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 14 ; Fig. 15		-	14.5	-	nC
Q_{GS}	gate-source charge	$I_D = 10 \text{ A}$; $V_{DS} = 32 \text{ V}$; $V_{GS} = 10 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 14		-	2	-	nC
Q_{GD}	gate-drain charge	$I_D = 10 \text{ A}$; $V_{DS} = 32 \text{ V}$; $V_{GS} = 10 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 14		-	3	-	nC
C_{iss}	input capacitance	$V_{DS} = 25 \text{ V}$; $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$;		-	796	1061	pF
C_{oss}	output capacitance	$T_j = 25 \text{ }^\circ\text{C}$; Fig. 16		-	137	164	pF
C_{rss}	reverse transfer capacitance			-	82	112	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 32 \text{ V}$; $R_L = 3.3 \Omega$; $V_{GS} = 10 \text{ V}$;		-	4	-	ns
t_r	rise time	$R_{G(\text{ext})} = 5 \Omega$; $T_j = 25 \text{ }^\circ\text{C}$		-	4.6	-	ns
$t_{d(off)}$	turn-off delay time			-	17.5	-	ns
t_f	fall time			-	9.9	-	ns

Source-drain diode FET1 and FET2

V_{SD}	source-drain voltage	$I_S = 10 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 17		-	0.78	1.2	V
t_{rr}	reverse recovery time	$I_S = 10 \text{ A}$; $dI_S/dt = -100 \text{ A}/\mu\text{s}$; $V_{GS} = 0 \text{ V}$;		-	8.3	-	ns
Q_r	recovered charge	$V_{DS} = 20 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$		-	16.2	-	nC

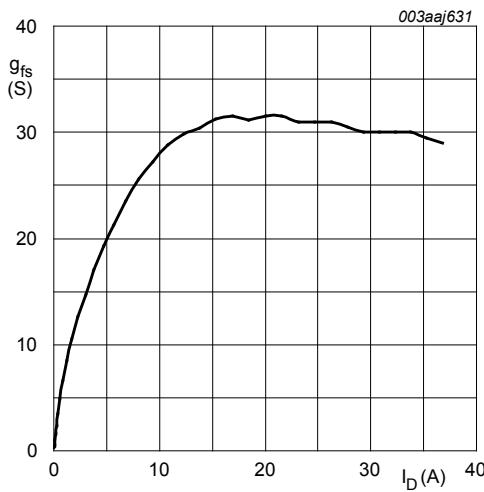


Fig. 6. Forward transconductance as a function of drain current; typical values

$T_j = 25 \text{ }^\circ\text{C}$; $V_{DS} = 5 \text{ V}$

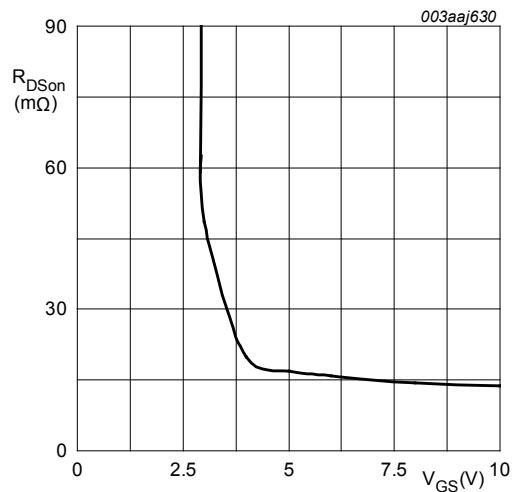
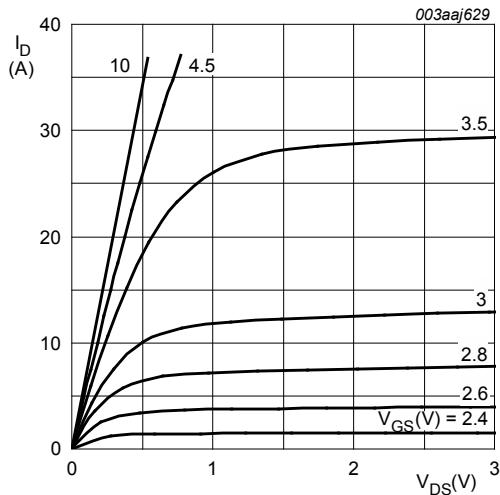


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25 \text{ }^\circ\text{C}$; $I_D = 10 \text{ A}$



$T_j = 25^\circ\text{C}$; $t_p = 300\ \mu\text{s}$

Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

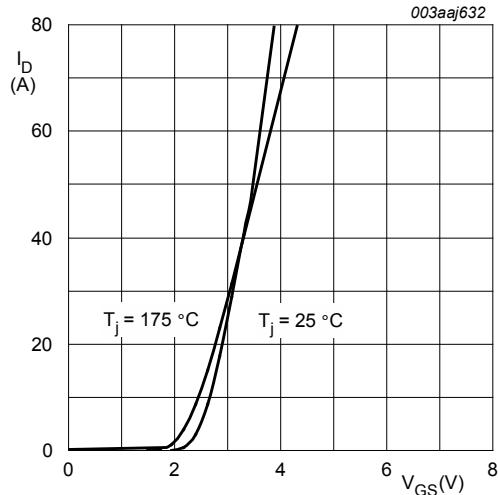


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{V}$

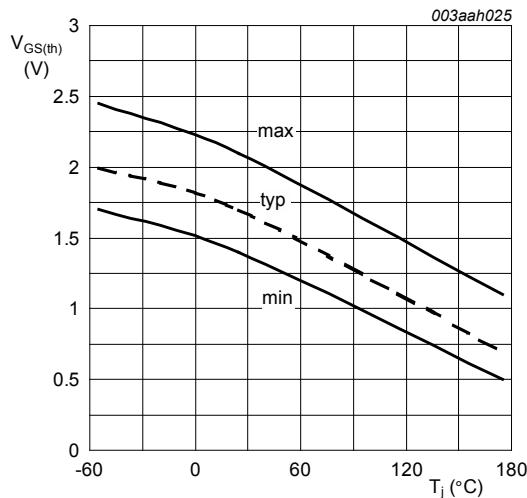


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$

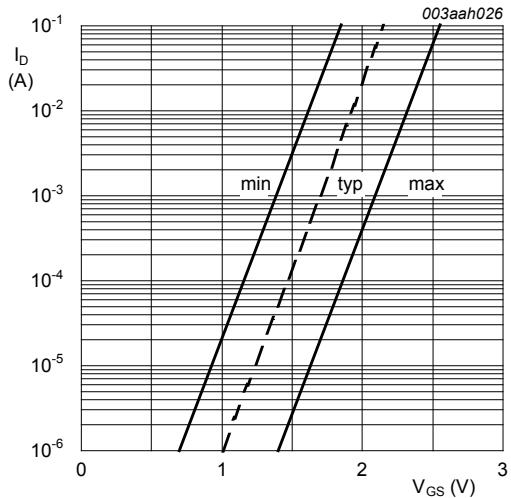
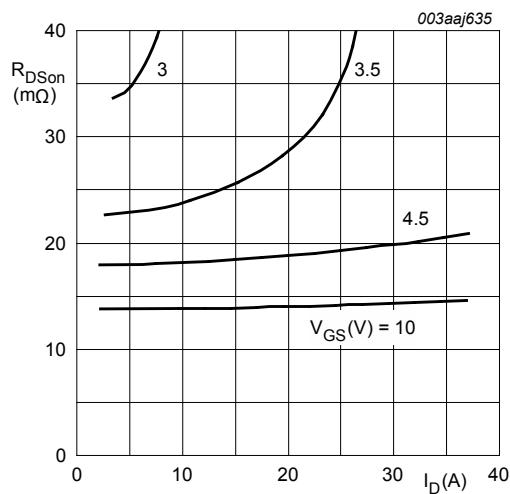


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}$; $V_{DS} = 5\text{V}$



$T_j = 25^\circ\text{C}$; $t_p = 300 \mu\text{s}$

Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

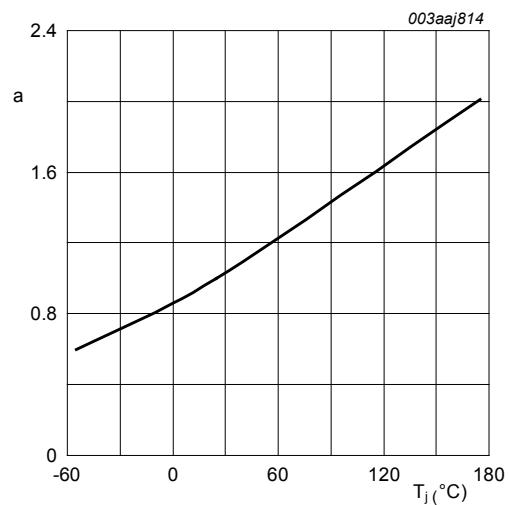


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

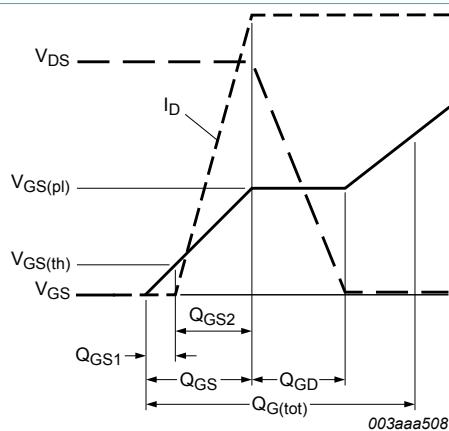


Fig. 14. Gate charge waveform definitions

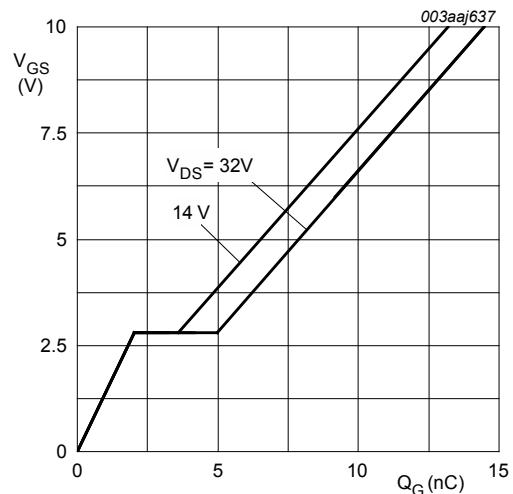


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ\text{C}$; $I_D = 10\text{A}$

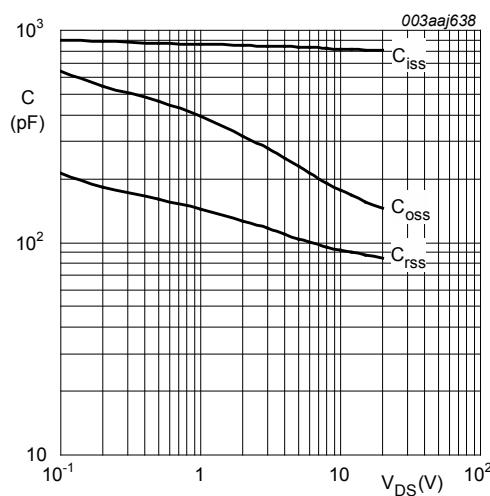


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V$; $f = 1MHz$

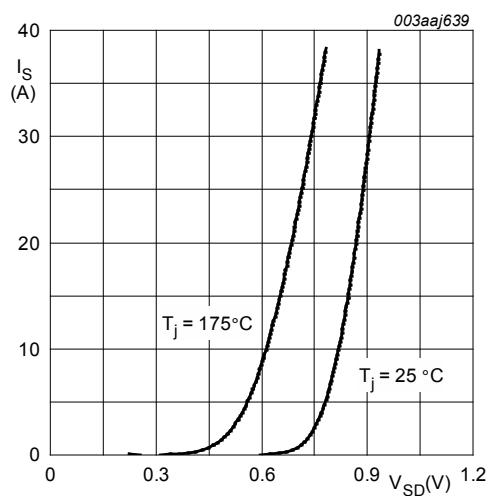
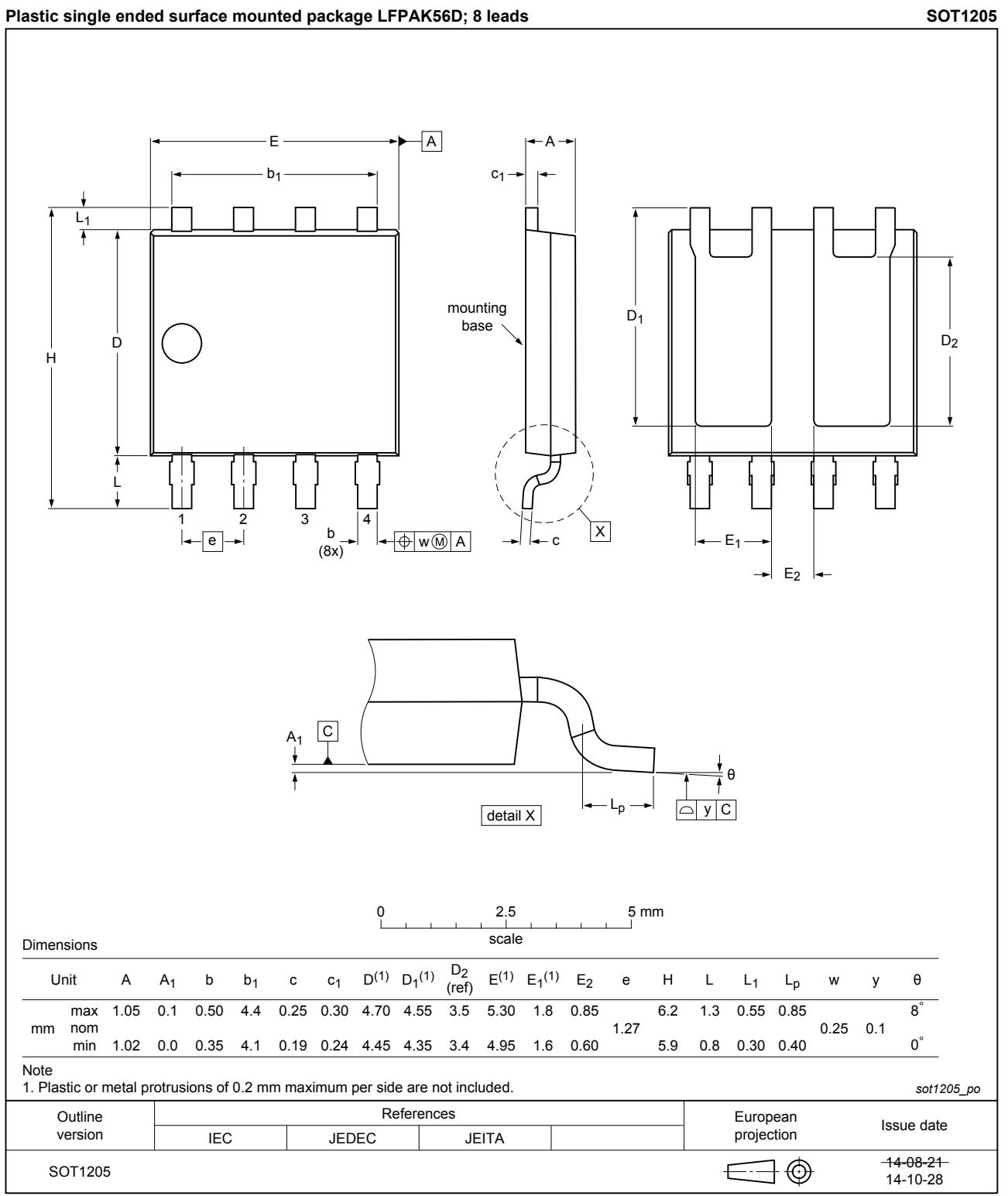


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

11. Package outline



12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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